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(71) Applicant: INL - INTERNATIONAL IBERIAN NANOTECHNOLOGY LABORATORY [PT/PT]; Avda. Mestre José Veiga s/n, 4715-330 Braga (PT).

(72) Inventors: SALOMÉ, Pedro; Avda. Mestre José Veiga s/n, 4715-330 Braga (PT). SADEWASSER, Sascha; Avda. Mestre José Veiga s/n, 4715-330 Braga (PT). MONTELIUS, Lars; Avda. Mestre José Veiga s/n, 4715-330 Braga (PT).

(74) Agent: AWAPATENT AB; Box 5117, 200 71 Malmö (SE).

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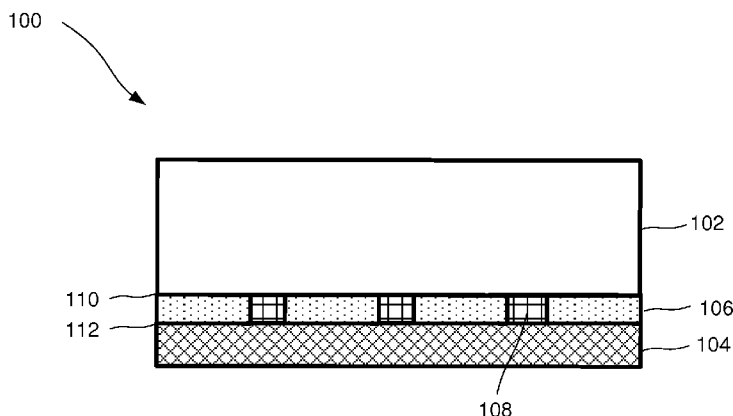


FIG. 1

(57) Abstract: The present invention relates to a material structure for a solar cell and a method for manufacturing the material structure. A solar cell comprising the material structure is also disclosed. The material structure (100) comprising, a light absorbing layer (102) being a semiconductor material, a metal layer (104), a passivation layer (106) arranged in between the light absorbing layer (102) and the metal layer (104), the passivation layer (106) comprising a plurality of electrical contacts (108), the electrical contacts (108) extending from a top surface (110) to a bottom surface (112) of the passivation layer (106) such that the electrical contacts (108) are in galvanic contact with the light absorbing layer (102) and the metal layer (104), wherein the electrical contacts (108) are formed by a first metal and the metal layer (104) is formed by a second metal, the second metal being different from the first metal.

A MATERIAL STRUCTURE FOR A SOLAR CELL, A SOLAR CELL AND A
METHOD FOR MANUFACTURING A MATERIAL STRUCTURE

Technical Field

The present invention relates to a material structure for a solar cell and a method for manufacturing the material structure. A solar cell comprising the
5 material structure is also disclosed.

Background Art

Solar cells convert solar energy into electrical energy. Cost effective large scale production of solar cells for efficient energy conversion is,
10 however, challenging. A conventional solar cell comprises a light absorbing layer arranged to absorb photons and to convert the energy of the photons into free charge carriers which are separated such that a potential difference is achieved. The light absorbing layer typically forms part of a pn-junction of the solar cell. Hence, radiation of an appropriate wavelength falling on to the
15 light absorbing layer may reach the pn-junction providing electron-hole pairs. A potential difference over the pn-junction is further obtained as holes and electrons move across the junction in opposite directions. An electric current may thereby be generated which may e.g. deliver electrical power to an external circuit.

20 A large cost when manufacturing a solar cell is the expensive materials used. To date, the market is dominated by solar cells based on crystalline silicon wafers onto which a light absorbing layer or layers comprising mono-crystalline or multi-crystalline silicon is/are arranged. These solar cells have high conversion efficiencies, but are expensive to manufacture and are brittle.

25 There are, however, other semiconductor materials that have advantageous photovoltaic characteristics. Compounds such as $\text{Cu}(\text{In,Ga})\text{Se}_2$, also referred to as CIGS, and CdTe may also be commercially used as light absorbing layers in solar cells. These compounds have higher absorption coefficients as compared to silicon. Therefore a lower thickness of
30 the light absorbing layer is needed to collect the same amount of photons as

compared to silicon based solar cells. Thinner and thereby more cost effective solar cells may hence be provided.

To access the electrical power generated by solar cells, electrodes are formed on the solar cells to extract charge carries from the pn-junction. The
5 electrodes may be formed by metalizing portions of the front- and back-sides of the solar cells.

Although a back side metal contact may provide efficient contacting to the light absorbing layer it may capture charge carries generated within the light absorbing layer. The back side metal contact may additional capture light
10 that has not been absorbed by the light absorbing layer.

To increase the efficiency of the solar cell a passivated emitter rear contact, PERC, structure may be used. The PERC structure comprises a passivation layer arranged in between the light absorbing layer and the metal contact. The passivation layer has openings through which the metal contact
15 may be brought in electrical contact with the light absorbing layer. The passivation layer of the PERC structure may thereby acts as a spacer layer mitigating that charge carriers from within the light absorbing layer are captured by the metal layer. In other words, the passivation layer may mitigate electron and/or hole recombination at defects and other
20 recombination sites that may occur at the interface between the light absorbing layer and the metal layer. The passivation layer may thereby assist in maintaining an electrical potential difference, across the light absorbing layer such that a solar cell with increased energy yield may be provided.

Hence, solar cells comprising PERC structures offer efficiency
25 enhancement, but require extra processing steps for depositing and patterning of the passivation layer. This further increases the costs for manufacturing the solar cells.

There is therefore a need to reduce material and manufacturing costs when manufacturing solar cells. There is also a need to increase the
30 efficiency of the solar cells to lower the cost per watt produced. To this end, methods which could be adapted to low-cost, high-volume manufacturing of solar cells are desirable.

Summary of the invention

It is an object of the present invention to provide an improvement of the above techniques and prior art.

According to an aspect of the invention, this is achieved by a material structure for a solar cell. The material structure comprising a light absorbing layer being a semiconductor material, a metal layer, a passivation layer arranged in between the light absorbing layer and the metal layer, the passivation layer comprising a plurality of electrical contacts, the electrical contacts extending from a top surface to a bottom surface of the passivation layer such that the electrical contacts are in galvanic contact with the light absorbing layer and the metal layer, wherein the electrical contacts are formed by a first metal and the metal layer is formed by a second metal, the second metal being different from the first metal.

A material structure in which the electrical contacts are formed with a reduced amount of material is thereby provided. This reduces the cost of the material structure. It is advantageous that the electrical contacts are formed by a first metal and the metal layer is formed by a second metal, the second metal being different from the first metal. Hence, the electrical contacts and the metal layer are formed by different materials or different combinations of materials which may be chosen independently of each other.

The material of the electrical contacts may therefore be chosen based on a first set of characteristics such as providing low resistivity, good adhesion, having low roughness, and being chemically inert to the material of the light absorbing layer and the passivation layer. The material of the metal layer may, however, be chosen based on a second set of characteristics allowing for a simplified manufacturing, a low resistivity, and providing an improved reflectivity as compared to the material of the electrical contacts. An increased portion of light may thus be reflected back into the light absorbing layer or out of the material structure, i.e. more light may be absorbed by the light absorbing layer. To this end, less light may be absorbed in the metal layer whereby the metal layer is heated to a lower extent which increases the performance of the material structure. The simplified manufacturing may reduce manufacturing costs as well as allowing for improved scalability of the

manufacturing. Further, the cost for manufacturing the material structure may also be reduced.

The wording *passivation layer* should be construed as a layer arranged on at least a portion of the metal layer. The passivation layer thereby acts as
5 a spacer layer mitigating that charge carriers from within the light absorbing layer are captured by the metal layer. The passivation layer reduces electron and/or hole recombination at the metal layer and/or at an interface between the metal layer and the light absorbing layer. In other words, the passivation layer assists in maintaining an electrical gradient, also referred to as a
10 difference in charge or an electrical potential difference, across the light absorbing layer.

The electrical contacts may comprise a metal. The electrical contacts may thereby provide efficient transfer of charges.

The electrical contacts are formed by a first metal, wherein the
15 electrical contacts may comprise molybdenum, Mo. The use of Mo is beneficial as Mo offers low resistivity, good adhesion, has low surface roughness, and is essentially chemically inert to materials such as e.g. Cu, In, Ga, Zn, Sn, S and Se which may form parts of the light absorbing layer. Mo furthermore forms an ohmic contact with the light-absorbing layer and has a
20 low diffusion coefficient. Mo is also stable during elevated temperatures which may for instance occur during the manufacturing of the material structure.

The passivation layer may comprise a dielectric material and/or a semiconductor material. The amount of charges originating from the light absorbing layer that are lost due to recombination at the interface between
25 the passivation layer and the light absorbing layer may thereby be reduced. The material structure may thereby reduce recombination losses resulting in an increased electrical performance. By selecting a specific dielectric material and/or a semiconductor material the passivation layer may further be tuned to reflect light within a desired energy range.

30 The metal layer is formed by a second metal, wherein the second metal is different from the first metal.

The metal layer may comprise Cu, Al, Ag, Mo, W, Cr, Ta, Nb, V, Ti, Mn, ZrN, TiN, Nb:TiO₂, TiB₂ or combinations thereof. The metal layer may

thereby be brought in galvanic contact with the electrical contacts. Efficient contacting of the material structure is thereby provided. The metal layer may thereby further comprise a material which provides high reflectance in the visible spectrum of light.

5 The light absorbing layer may be a compound semiconductor material consisting of Cu(In, Ga)Se₂, Cu(In, Ga)(S, Se)₂, Cu₂ZnSn(S, Se)₄, or CdTe.

 These semiconductor materials are advantageous to use as efficient absorption of light may be achieved within the light absorbing layer when using these materials. Materials comprising Cu, In and Se may form a thin
10 layer that provides high absorption of light to be absorbed in a micron or few microns of the materials. Ga further increases the spectral window for light absorption. The absorption energies of the light absorbing layer may match the solar spectrum. An improved efficiency for absorbing light is thereby obtained.

15 The material structure may further comprise a substrate, wherein the metal layer is arranged on the substrate. The substrate provides improved handling to the material structure. The metal layer may further allow for heat transfer from the metal layer such that heating of the material structure is mitigated. An improved thermal management of the material structure may
20 thereby be provided.

 The material structure may further comprise a buffer layer, the buffer layer and the light absorbing layer forming parts of a pn-junction arranged to convert light to an electric voltage. Efficient separation of charge carriers generated by the light absorbed by the material structure may thereby be
25 obtained.

 According to a second aspect of the invention a solar cell comprising the material structure is provided. A solar cell with improved efficiency may thereby be obtained. The manufacturing cost of the solar cell may further be reduced. Advantages of using the above disclosed material structure will for
30 brevity not be disclosed again. The above mentioned features, when applicable apply to the solar cell and reference is made to the above.

 According to a third aspect method for manufacturing a material structure for a solar cell is provided. The method comprises the steps of

providing a substrate comprising a metal layer, depositing a passivation layer on the metal layer, depositing an imprint polymer on the passivation layer, imprinting the imprint polymer by means of nano-imprint lithography, NIL, using a template, thereby forming openings in the imprint polymer extending
5 from a top surface to a bottom surface thereof, etching the passivation layer using the imprinted imprint polymer as an etch mask thereby forming openings in the passivation layer extending from a top surface to a bottom surface thereof, forming electrical contacts in the openings in the passivation layer, the electrical contacts being in galvanic contact with the metal layer,
10 removing the imprinted imprint polymer thereby exposing at least a portion of the passivation layer, depositing a light absorbing layer being a semiconductor material on the passivation layer, the light absorbing layer being in galvanic contact with the electrical contacts, wherein the electrical contacts are formed by a first metal and the metal layer is formed by a second
15 metal, the second metal being different from the first metal.

The method is advantageous in that a material structure may be manufactured cost effectively with high throughput and high resolution. Nano-imprint lithography, moreover, provides openings in the passivation layer that may have diameters in the range of tens to hundreds of nanometers wherein
20 the electrical contacts may be formed. An efficient passivation layer is thereby provided which offers increased surface coverage such that electron and/or hole recombination at the metal layer and/or at an interface between the metal layer and the light absorbing layer may be reduced. The wording *template* should be understood as a *mould*, also referred to as a stamp
25 having a pattern. The pattern is transferred to the imprint polymer by mechanical deformation of the imprint polymer by pressing the template into the imprint polymer. Subsequent processes such as etching of the passivation layer using the imprinted imprint polymer as an etch mask may be performed. The instrumentation and materials used for NIL may vary as is
30 known to the skilled person in the art.

The height of the pattern of the template should preferably be larger than the thickness of imprint polymer such that the openings formed in the imprint polymer during the imprint process extend from a top surface to a

bottom surface of the imprint polymer. The wording *extend from a top surface to a bottom surface* of the imprint polymer should be construed as that the openings essentially stretch out in distance through the imprint polymer. The skilled person in the art knows that a residual layer may, however, in practice
5 be present in openings as a result of the imprint technique.

The wording *exposing at least a portion of the passivation layer* should be understood as substantially exposing the passivation layer in a desired surface area. The skilled person in the art realizes that the surface area may be a given area of the material structure or substantially the whole material
10 structure.

The forming of the electrical contacts may comprise selective deposition of a metal. By the wording *selective deposition* should be understood that metal is deposited at given desired locations in the material structure, i.e. in the openings in the passivation layer and for instance not on
15 the passivation layer itself. The metal may thereby be essentially arranged only in the openings of the passivation layer. Selective deposition may be performed by different techniques such as electroplating and ink-jet printing.

The step of removing the imprinted imprint polymer may be performed prior to the step of forming of the electrical contacts.

20 This is advantageous as the risk is reduced that a material used for forming the electrical contacts sticks to the imprinted imprint polymer. Problems associated with the imprinted imprint polymer being bound to the material structure are thereby mitigated. Furthermore, the amount of material used for forming the electrical contacts may be reduced. A more efficient
25 process for removing the imprinted imprint polymer is thereby obtained.

The forming of the electrical contacts may comprise sputtering and/or evaporation of a metal. A simple, cost effective and reliable method for providing electrical contacts of metals may thereby be used.

The step of removing the imprinted imprint polymer may be performed
30 using a lift-off process.

The wording *lift-off* may be understood as a process of forming structures or patterns on a material surface of, e.g. the passivation layer by using a sacrificial layer, e.g. a layer of imprint polymer. In general, a pattern is

formed in the sacrificial layer arranged on the material surface. By etching through the sacrificial layer openings are formed in the sacrificial layer exposing portions of the material surface. A target material may in a subsequent process be deposited, through the openings, on the material surface such that a final pattern may be created at those locations. The target material is typically deposited over the whole area of the sacrificial layer, reaching the material surface in the etched openings but also on top of the sacrificial layer where it has not been etched. The sacrificial layer may then be washed away such that the target material on the top of the sacrificial layer is lifted-off and washed away together with the sacrificial layer below. After the lift-off, the target material remains in the regions where it had a direct contact with the material surface.

The method further comprises depositing a light absorbing layer on the passivation layer, the light absorbing layer being in galvanic contact with the electrical contacts. As a result a material structure is obtained which is suitable for absorbing light. The electrical contacts are further arranged to collect charge carriers generated within the light absorbing layer.

The method may further comprise depositing a buffer layer on the light absorbing layer, the buffer layer and the light absorbing layer forming parts of a pn-junction arranged to convert light to an electric voltage. Efficient separation of charge carriers generated by the light absorbed by the material structure may thereby be obtained. A material structure for a solar cell which is arranged to absorb light and convert optical energy into electrical energy is thereby achieved.

Further features of, and advantages with, the present invention will become apparent when studying the appended claims and the following description. The skilled person will realize that different features of the present invention may be combined to create embodiments other than those described in the following, without departing from the scope of the present invention.

Brief description of the drawings

This and other aspects of the present invention will now be described in more detail, with reference to the enclosed drawings showing embodiments of the invention.

Figure 1 illustrates a material structure according to one embodiment
5 of the present invention.

Figure 2 illustrates a method for manufacturing a material structure according to one embodiment of the present invention.

Figure 3 illustrates pre-stages of and a material structure according to one embodiment of the present invention.

10 Figure 4 illustrates pre-stages of and a material structure according to another embodiment of the present invention.

Figure 5 illustrates pre-stages of and a material structure according to yet another embodiment of the present invention.

15 Figure 6 illustrates a solar cell according to one embodiment of the present invention.

Detailed description

The present invention will now be described more fully hereinafter with
20 reference to the accompanying drawings, in which currently preferred embodiments of the invention are shown. This invention may, however, be embodied in many different forms and should not be construed as limited to the embodiments set forth herein. These embodiments are rather provided for thoroughness and completeness, and for fully conveying the scope of the
25 invention to the skilled person.

In the following a material structure for a solar cell and a method for manufacturing the material structure will be discussed with reference to figures 1 – 3. Figure 1 illustrates a material structure for a solar cell. The material structure 100 comprises a light absorbing layer 102, a metal layer
30 104 and a passivation layer 106. The passivation layer 106 is arranged in between the light absorbing layer 102 and the metal layer 104. A plurality of electrical contacts 108 are arranged within the passivation layer 106. The electrical contacts 108 extend from a top surface 110 to a bottom surface 112

of the passivation layer 106. The electrical contacts 108 are thereby in galvanic contact with the light absorbing layer 102 and the metal layer 104 allowing electrical currents to flow between the layers 102 and 104.

The electrical contacts 108 are formed by a first metal. The metal layer 5 104 is formed by a second metal, wherein the second metal is different from the first metal.

The material of the electrical contacts 108 may therefore be chosen based on a first set of characteristics such as providing low resistivity, good adhesion, having low roughness, and being chemically inert to the material of 10 the light absorbing layer and the passivation layer. The material of the metal layer 104 may, however, be chosen based on a second set of characteristics allowing for a simplified manufacturing, a low resistivity, and providing an improved reflectivity as compared to the material of the electrical contacts.

To this end, the electrical contacts 108 comprise molybdenum, Mo.

15 The metal layer 104 comprises copper, Cu. The passivation layer 106 comprises Al_2O_3 . The use of Al_2O_3 allows for an isolating passivation layer 106 having a large concentration of fixed charges, which may be deposited conformally on top of the metal layer 104. The light absorbing layer 102 comprises $\text{Cu}(\text{In}, \text{Ga})\text{Se}_2$, also referred to as CIGS. The CIGS light absorbing 20 layer 102 has a higher absorption coefficient than silicon and therefore a lower thickness of the light absorbing layer is needed to collect the same amount of photons as compared to silicon based solar cells.

The Mo electrical contacts 108 offer low resistivity, good adhesion to the light absorbing layer 102. Mo is moreover essentially chemically inert to 25 the materials Cu, In, Ga, and Se of the CIGS material, even at elevated temperatures such as a CIGS high-temperature selenization process at which the temperature may be above 500°C . It may be noted that at such temperatures a thin MoSe_2 layer may be formed on the Mo electrical contacts 108 which further improves the conducting properties of the electrical 30 contacts 108. Mo furthermore allows for the formation of ohmic contacts to the light-absorbing layer 102. Mo also has a low diffusion coefficient which makes the material stable even at elevated temperatures. Elevated temperatures may for instance occur during the manufacturing of the material

structure 100. The performance of the material structure 100 may thereby be improved.

From the above it follows that it is favourable that the materials forming the electrical contacts 108 and the metal layer 104 are different such that their
5 respective functions may be optimized. As a result a material structure 100 for a solar cell with an increased efficiency may be obtained. A metal layer 104 comprising for instance Cu provides high reflectance in the visible spectrum such that light may be reflected into the light absorbing layer.

The increased reflectivity provided by Cu metal layer 104 increase the
10 amount of light on the material structure 100 that may be absorbed by the light absorbing layer 102. The thickness of the light absorbing layer 102 may thereby be reduced and thinner and more cost effective solar cells may be provided with respect to solar cells not comprising the material structure 100.

Cu also allows for cost effective manufacturing of the material structure
15 100 as compared to the metal layer comprising Mo. In other words, a material structure 100 comprising a lower amount of Mo may thereby be obtained. The costs associated with material forming the material structure 100 may thereby be reduced.

A metal layer 104 comprising Cu further offers improved performance
20 of the material structure 100. The Cu metal layer 104 provides increased thermal conductivity and an increased electrical conductivity.

It should be noted that the electrical contacts 108 may be formed by molybdenum, Mo and the metal layer 104 may be formed by Cu.

The Al₂O₃ passivation layer 106 increases the efficiency of the material
25 structure in that it may reduce losses due to recombination.

The Al₂O₃ passivation layer 106 further acts as a spacer layer between the light absorbing layer 102 and the metal layer 104 in that it alleviates that charge carriers, generated by light absorption in the light absorbing layer 102, are captured by the metal layer 104. The Al₂O₃ passivation layer may thereby
30 reduce electron and/or hole recombination at the interface between the metal layer 104 and the light absorbing layer 102. An improved electrical gradient across the light absorbing layer 102 may thereby be achieved resulting in that a higher electrical potential is generated. A more efficient conversion of

optical energy to electrical energy may thereby be achieved by the material structure 100.

Next a method 200 for manufacturing the material structure 100 will be described with reference to figures 2 and 3. Figure 2 illustrates method steps
5 whereas figure 3 illustrates pre-stages 300 of the material structure and material structure 100 achieved by performing the method 200.

The method 200 comprises the steps of providing 202 a substrate 302 onto which a metal layer 104 has been formed. The substrate comprises soda-lime glass, but the skilled person realizes that other substrates may be
10 used as will be described below.

A passivation layer 106 is thereafter deposited 204 on the metal layer 104, followed by deposition 206 of an imprint polymer 304 on the passivation layer 106. The deposition 204 may be performed by atomic layer deposition, ALD. The deposition 206 may be performed by standard techniques such as
15 spin-coating also referred to as spin-casting.

Nano-imprint lithography, NIL, is used to form a pattern in the passivation layer 106. In NIL the imprint polymer 304 is imprinted 208 using a template, also referred to as mold or stamp. The template comprises patterns, for example nanostructured patterns, which are transferred to the imprint
20 polymer 304 when the template is pressed into the imprint polymer 304. In other words, the pressing of the template into the imprint polymer 304 creates an inverse pattern of the template resulting in that the imprint polymer 304 has a varying thickness.

The template may for example comprise silicon dioxide or silicon.
25 Other materials such as metals and ceramics may also be used for the template. The template may for instance be patterned using electron beam lithography and reactive ion etching, RIE.

The template is removed after the imprint polymer has been imprinted, i.e. after the pattern of the template has been transferred into the imprint
30 polymer 304. An anisotropic etching process, such as reactive ion etching, RIE, may further be used to remove residuals of the imprint polymer 304 in the area forming openings, i.e. the compressed area. During the imprint step, the imprint polymer 304 may be heated to a temperature above its glass

transition temperature. The imprint polymer 304 may be a thermoplastic or thermosetting polymer which becomes a viscous liquid which can flow when heated, and therefore, be readily deformed when imprinted with the template. Generally, the imprint polymer 304 is cooled such that the imprint polymer
5 304 solidifies before the template is removed. A more effective transfer of the pattern of the template into the imprinted imprint polymer 304 may thereby be obtained.

Openings 306 in the imprint polymer 304 are thereby formed by the imprint process.

10 It should be noted that the resolution of NIL, unlike conventional lithography methods such as electron beam lithography and optical lithography using energetic beams, is not limited by the effects of wave diffraction, scattering and interference in a resist, i.e. the imprint polymer, and backscattering from the substrate. An improved resolution for manufacturing
15 features on the nanoscale may thereby be obtained. Beam scanning is moreover not needed in NIL which improves the speed for manufacturing the material structure. Hence, NIL offers high-resolution high-throughput lithography which may be used for low-cost mass production of nanostructures over large areas.

20 Next, the passivation layer 106 may be etched 210 using the imprinted imprint polymer 304 as an etch mask 308 such that openings 310 are formed in the passivation layer 106. The openings 310 extend from a top surface 110 to a bottom surface 112 of the passivation layer 106. The etching may be performed using reactive ion etching.

25 After the openings 310 in the passivation layer 106 have been provided electrical contacts 108 may be formed 212 in the openings 310. The electrical contacts 108 may be formed by different processes as will be described below. The electrical contacts 108 should, however, be in galvanic contact with the metal layer 104.

30 The imprinted imprint polymer 304 may then be removed 214 thereby exposing at least a portion of the passivation layer 106. The imprinted imprint polymer 304 may be removed by a standard heated polymer "remover". Typically an ultrasonic bath is used during the removal together with an

organic element such as acetone or a commercially available polymer remover. Techniques such as O₂-plasma treatment may further be used for the removing 214.

The electrical contacts 108 may be formed 212 using sputtering and/or
5 evaporation of a metal as illustrated by the pre-stage 400 of the material structure shown in figure 3. Methods for depositing materials such as metals are known in the field of the art and will not be discussed further. Sputtering and/or evaporation of the metal, before the imprinted imprint polymer 304 is removed 214, results in that metal 312 may be deposited on at least a portion
10 of the imprinted imprint polymer 304. The electrical contacts 108 extend preferably through the passivation layer 106.

The removing 214 of the imprinted imprint polymer may be performed using a lift-off process. The lift-off of the imprinted polymer layer may be performed by soaking the substrate in acetone or a remover in an ultrasonic
15 bath. The imprinted imprint polymer 106 and the metal 312 may thereby be efficiently removed by the lift-off. The resulting pre-stage 500 of the material structure is shown in figure 3. Methods and recipes for lift-off is known to a skilled person in the art and reference may for example be given to Carlberg *et al*, "*Lift off process for nanoimprint lithography*", Microelectronic
20 Engineering 67-68, p 203 (2003).

Now referring to figure 4, the forming of the electrical contacts 108 may comprise selective deposition of a metal 314. The metal 314 may thereby be formed essentially only in the openings 310 of the passivation layer 106, as illustrated by the pre-stage 600 of the material structure. The selective
25 deposition of a metal 314 may be achieved by electroplating. Electroplating is a well-known technique within the field of nanoprocessing which may take advantage of the imprint polymer 106 being an insulator such that the metal is deposited primarily on surfaces of the metal layer 104 that are exposed in the openings 310. The electrical contacts 108 extend through the passivation
30 layer 106.

The imprinted imprint polymer 304 may then be removed 214 as described above, thereby exposing at least a portion of the passivation layer 106.

Now referring to figure 5, the removing 214 of the imprinted imprint polymer 106 may alternatively be performed prior to the step of forming 212 of the electrical contacts 108, which results in that the pre-stage 700 of the material structure is obtained.

- 5 The electrical contacts 108 may thereafter be formed as described above by selective deposition such that the pre-stage 500 of the material structure is formed.

 The imprint polymer 106 may comprise polymethyl methacrylate, PMMA. PMMA has a small and advantageous thermal expansion coefficient
10 and a small pressure shrinkage coefficient. Template release agents may further be added into the imprint polymer to reduce adhesion to the template. Also to template may be anti-sticking treated to facilitate its removal from the imprint polymer.

 The skilled person in the art realises that UV-curable imprint polymers
15 may be used when fabricating the material structure. In this case an irreversible cross-linked imprint polymer is used.

 The method 200 further comprises depositing 216 a light absorbing layer 102 on the passivation layer 106 whereby the material structure 100 is obtained on a substrate 302, see figures 2 and 6. The light absorbing layer
20 102 may be brought in galvanic contact with the metal layer 104, via the electrical contacts 108, as a result of the electrical contacts 108 extending through the passivation layer 106.

 The method 200 may further comprise depositing a buffer layer 802 on the light absorbing layer 102 as is illustrated in figure 6, where a solar cell 800
25 comprising the material structure 100 is arranged on a substrate 302. The light absorbing layer 102 is composed of CIGS which is p-type. The buffer layer 802 comprises a CdS material which is n-type. The light absorbing layer 102 and the buffer layer 802 thereby form parts of a pn-junction arranged to convert light to an electric voltage. The buffer layer 802 may further form part
30 of a stack of layers 803 as illustrated in figure 6. The stack of layers 803 may comprise a transparent conducting layer 804 arranged on top of the buffer layer 802. The transparent conducting layer 804 comprises in the depicted embodiment a i-ZnO/ZnO:Al material, i.e. a thin, intrinsic zinc oxide layer (i-

ZnO) which is capped by a thicker, aluminium, Al, doped ZnO layer. The i-ZnO layer is used to protect the CdS buffer layer 802 and the light absorbing layer 102 from sputtering damage while depositing the ZnO:Al layer. The Al doped ZnO serves as a transparent conducting oxide to collect and move
5 electrons out of the solar cell 800 while absorbing as little light as possible.

The solar cell 800 comprises a heterostructure junction formed between the CIGS light absorbing layer 102 and the transparent conducting layer 804 of ZnO, which are separated by the thin buffer layer 802 of CdS and a layer of intrinsic ZnO. The CIGS light absorbing layer 102 is doped p-type
10 by intrinsic defects, while the ZnO transparent conducting layer 804 is doped n-type to a much larger extent through the incorporation of Al. This asymmetric doping provides a space-charge region extend to a larger extent into the CIGS than into the ZnO. The absorption of light is thereby designed to predominately occur in the light absorbing layer 102. To this end, the
15 thicknesses and band gaps of the light absorbing layer 102, the buffer layer 802, and the transparent conducting layer 804 are chosen such that the light is absorbed predominately in the light absorbing layer 102. The band gap of the CIGS light absorbing layer 102 ranges typically between 1.02 eV for CuInSe_2 to 1.65 eV for CuGaSe_2 providing increased light absorption, while
20 the larger band gaps for ZnO of 3.2 eV and CdS of 2.4 eV minimizes light absorption in the upper layers 802 and 804. The doped ZnO also serves as front contact for current collection.

The metal layer 104 comprises Cu, typically 0.5 – 5 μm thick onto which the passivation layer 106 has been deposited to decrease charge
25 recombination at the interface of the metal layer 104 and increase internal reflection. The passivation layer 106 comprises Al_2O_3 deposited by means of atomic layer deposition, ALD, on to the metal layer 104. The passivation layer 106 further comprises electrical contacts 108 of Mo which may be formed as described above.

30 The substrate 302 comprises soda lime glass as a substrate and contains sodium, which has been shown to yield a substantial open-circuit voltage increase through surface and/or grain boundary defects passivation. The substrate may have a thickness of 1–3 mm.

The CdS buffer layer may be deposited using a standard chemical bath deposition, CBD, process. The transparent conducting layer 804 may be formed using shunt reducing intrinsic ZnO layer, i-ZnO, and subsequently sputtering of Al-doped ZnO, ZnO:Al.

- 5 The stack of layers 803 may further comprise anti-reflective coating, not shown, which may be formed by evaporation to improve light absorption of the solar cell, mainly by avoiding interference effects.

A front contact grid comprising a Ni/Al/Ni stack, not shown, may further be deposited by evaporation.

- 10 The buffer layer may alternatively comprise a material selected from a group consisting of $\text{Zn}_{1-x}\text{Sn}_x\text{O}_y$, In_2S_3 , $\text{Zn}(\text{S},\text{O},\text{OH})$, $\text{Zn}(\text{S},\text{O})$, InS_xO_y , ZnS , $\text{ZnS}:\text{In}_2\text{S}_3$, In_xS_y .

The transparent conductive layer may, moreover, comprise a material selected from a group consisting of Ga-doped ZnO, $\text{SnO}_2:\text{In}_2\text{O}_3$, $\text{SnO}_2:\text{F}$,

- 15 CdO:In, graphene, and carbon nano-tubes.

According to the above description the metal layer 104 has been disclosed as comprising Cu. In other embodiments the metal layer may comprise Al, Ag, Mo, W, Cr, Ta, Nb, V, Ti, Mn, ZrN, TiN, Nb:TiO₂, TiB₂ or combinations thereof.

- 20 The passivation layer 106 has been described as to comprise Al₂O₃. According to other embodiments the passivation layer may be selected from a group consisting of dielectric materials such as Al₂O₃, SiO₂, Al₂N₃, Si₃N₄, AlON, TiO₂, HfO₂.

- 25 Alternatively the passivation layer may comprise a semiconductor material such as ZnO, InS, In₂O₃, BeO, AlN, BN, GaP.

The light absorbing layer may further comprise a compound semiconductor material consisting of Cu(In, Ga)(S, Se)₂, Cu₂ZnSn(S, Se)₄, or CdTe.

- 30 The person skilled in the art further realizes that the present invention by no means is limited to the preferred embodiments described above. On the contrary, many modifications and variations are possible within the scope of the appended claims. For example, the substrate may be a glass material

such as alkali-aluminosilicate glass or boro-silicate glass. The substrate may alternatively comprise a metal foil, a ceramic substrate, or a plastic substrate.

The light absorbing layer may alternatively be a compound semiconductor material comprising a plurality of other elements from the periodic table. The light absorbing layer may be of a group IV element such as Si, amorphous Si, nanocrystalline silicon or micromorphous silicon.

The light absorbing layer may comprise a III-V or a II-VI semiconductor material. Hence the light absorbing layer may in some embodiments for example comprise GaAs, and InP. The light absorbing layer may be of a material having a perovskite crystal structure.

The substrate may form the metal layer.

The light absorbing layer may be formed from by a chalcopyrite or a kesterite material. For such materials the substrate may be a sheet of glass or foil. The glass substrate may for example have a dimension of 80 cm x 120 cm. The foil may typically be arranged in a roll of a specific width, which may be 1 m in extension.

It should further be noted that the method described above may be used to provide electrical contacts and a metal layer comprising the same material compositions or different materials compositions. Hence a versatile method is provided.

Additionally, variations to the disclosed embodiments can be understood and effected by the skilled person in practicing the claimed invention, from a study of the drawings, the disclosure, and the appended claims. In the claims, the word "comprising" does not exclude other elements or steps, and the indefinite article "a" or "an" does not exclude a plurality. The mere fact that certain measures are recited in mutually different dependent claims does not indicate that a combination of these measures cannot be used to advantage.

CLAIMS

1. A material structure for a solar cell, the material structure (100)
5 comprising,
a light absorbing layer (102) being a semiconductor material,
a metal layer (104),
a passivation layer (106) arranged in between the light absorbing layer
(102) and the metal layer (104), the passivation layer (106) comprising a
10 plurality of electrical contacts (108), the electrical contacts (108) extending
from a top surface (110) to a bottom surface (112) of the passivation layer
(106) such that the electrical contacts (108) are in galvanic contact with the
light absorbing layer (102) and the metal layer (104), wherein the electrical
contacts (108) are formed by a first metal and the metal layer (104) is formed
15 by a second metal, the second metal being different from the first metal.
2. The material structure according to claim 1, wherein the electrical
contacts (108) comprise molybdenum, Mo.
- 20 3. The material structure according to claim 1 or 2, wherein the
passivation layer (106) comprises a dielectric material and/or a
semiconductor material.
4. The material structure according to any one of claims 1 – 3, wherein
25 the metal layer (104) comprises Cu, Al, Ag, Mo, W, Cr, Ta, Nb, V, Ti, Mn, ZrN,
TiN, Nb:TiO₂, TiB₂ or combinations thereof.
5. The material structure according to any one of claims 1 – 4, wherein
the light absorbing layer (102) is a compound semiconductor material
30 consisting of Cu(In, Ga)Se₂, Cu(In, Ga)(S, Se)₂, Cu₂ZnSn(S, Se)₄, or CdTe.

6. The material structure according to any one of claims 1 – 5, further comprising a substrate (302), wherein the metal layer (104) is arranged on the substrate (302).
- 5 7. The material structure according to any one of claims 1 – 6, further comprising a buffer layer (802), the buffer layer (802) and the light absorbing layer (102) forming parts of a pn-junction arranged to convert light to an electric voltage.
- 10 8. A solar cell comprising a material structure according to any one of claims 1 – 7.
9. A method for manufacturing a material structure for a solar cell, the method (200) comprising the steps of
- 15 providing (202) a substrate (302) comprising a metal layer (104),
depositing (204) a passivation layer (106) on the metal layer (104),
depositing (206) an imprint polymer (304) on the passivation layer (106),
imprinting (208) the imprint polymer (304) by means of nano-imprint
- 20 lithography, NIL, using a template, thereby forming openings (306) in the imprint polymer (304) extending from a top surface to a bottom surface thereof,
etching (210) the passivation layer (106) using the imprinted imprint polymer (304) as an etch mask thereby forming openings (310) in the
- 25 passivation layer (106) extending from a top surface (110) to a bottom surface (112) thereof,
forming (212) electrical contacts (108) in the openings (310) in the passivation layer (106), the electrical contacts (108) being in galvanic contact with the metal layer (104),
- 30 removing (214) the imprinted imprint polymer (304) thereby exposing at least a portion of the passivation layer (106),

depositing (216) a light absorbing layer (102) being a semiconductor material on the passivation layer (106), the light absorbing layer (102) being in galvanic contact with the electrical contacts (108),

- 5 wherein the electrical contacts (108) are formed by a first metal and the metal layer (104) is formed by a second metal, the second metal being different from the first metal.

10 10. The method according to claim 9, wherein the forming (212) of the electrical contacts (108) comprises selective deposition of a metal (314).

11. The method according to claim 9, wherein the step of removing (214) the imprinted imprint polymer (304) is performed prior to the step of forming (212) of the electrical contacts (108).

15 12. The method according to claim 9, wherein the forming (212) of the electrical contacts (108) comprises sputtering and/or evaporation of a metal.

13. The method according to claim 12, wherein the step of removing (214) the imprinted imprint polymer (304) is performed using a lift-off process.

20 14. The method according to claim 9, the method (200) further comprising depositing a buffer layer (802) on the light absorbing layer (102), the buffer layer (802) and the light absorbing layer (102) forming parts of a pn-junction arranged to convert light to an electric voltage.

25

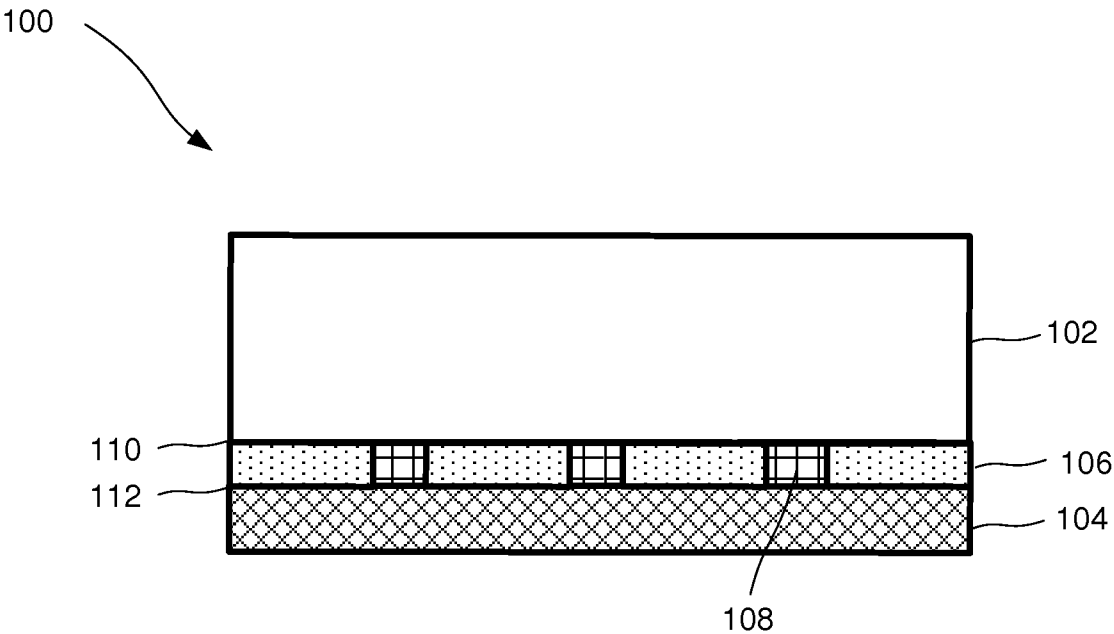
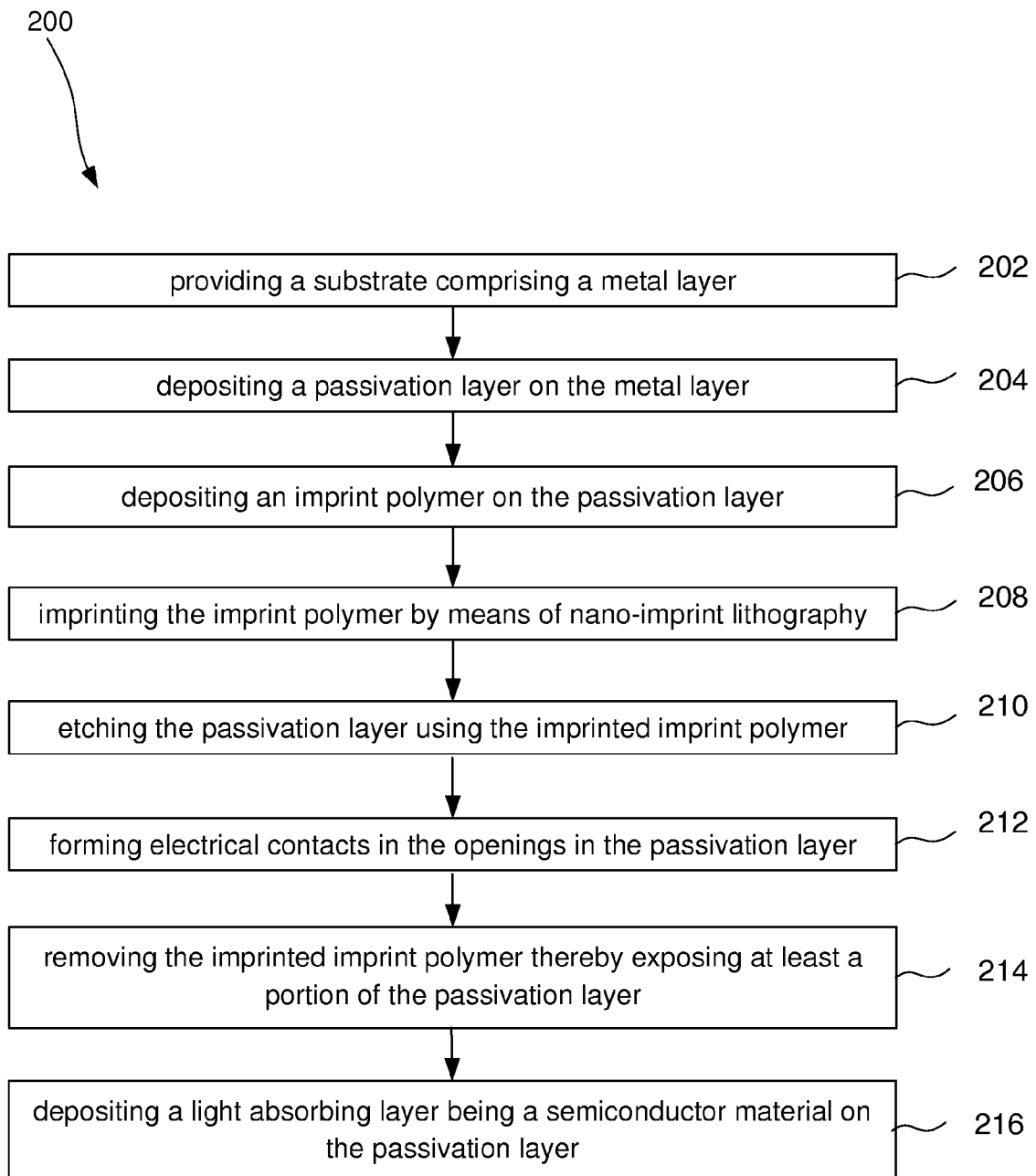


FIG. 1

2/6

**FIG. 2**

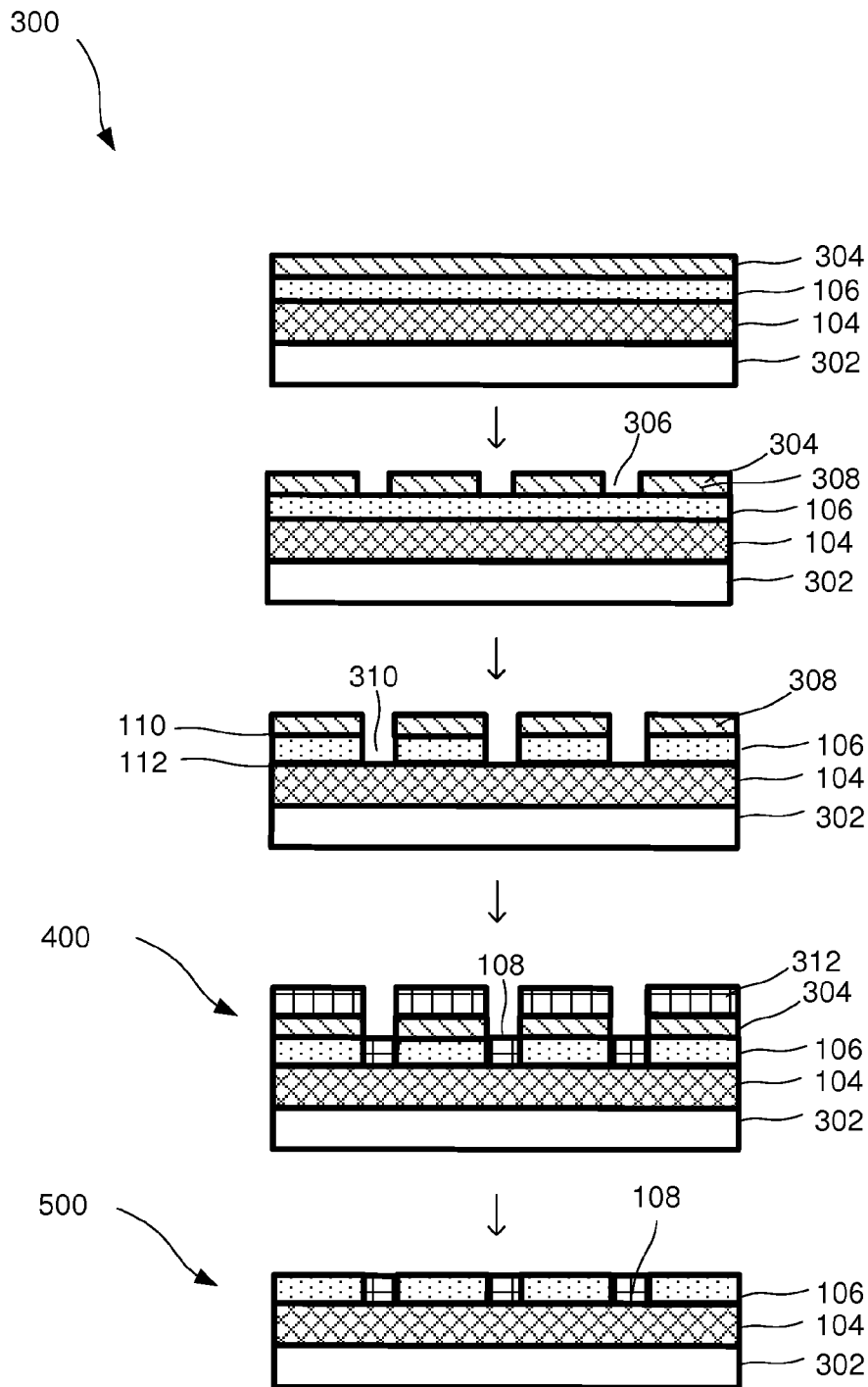


FIG. 3

4/6

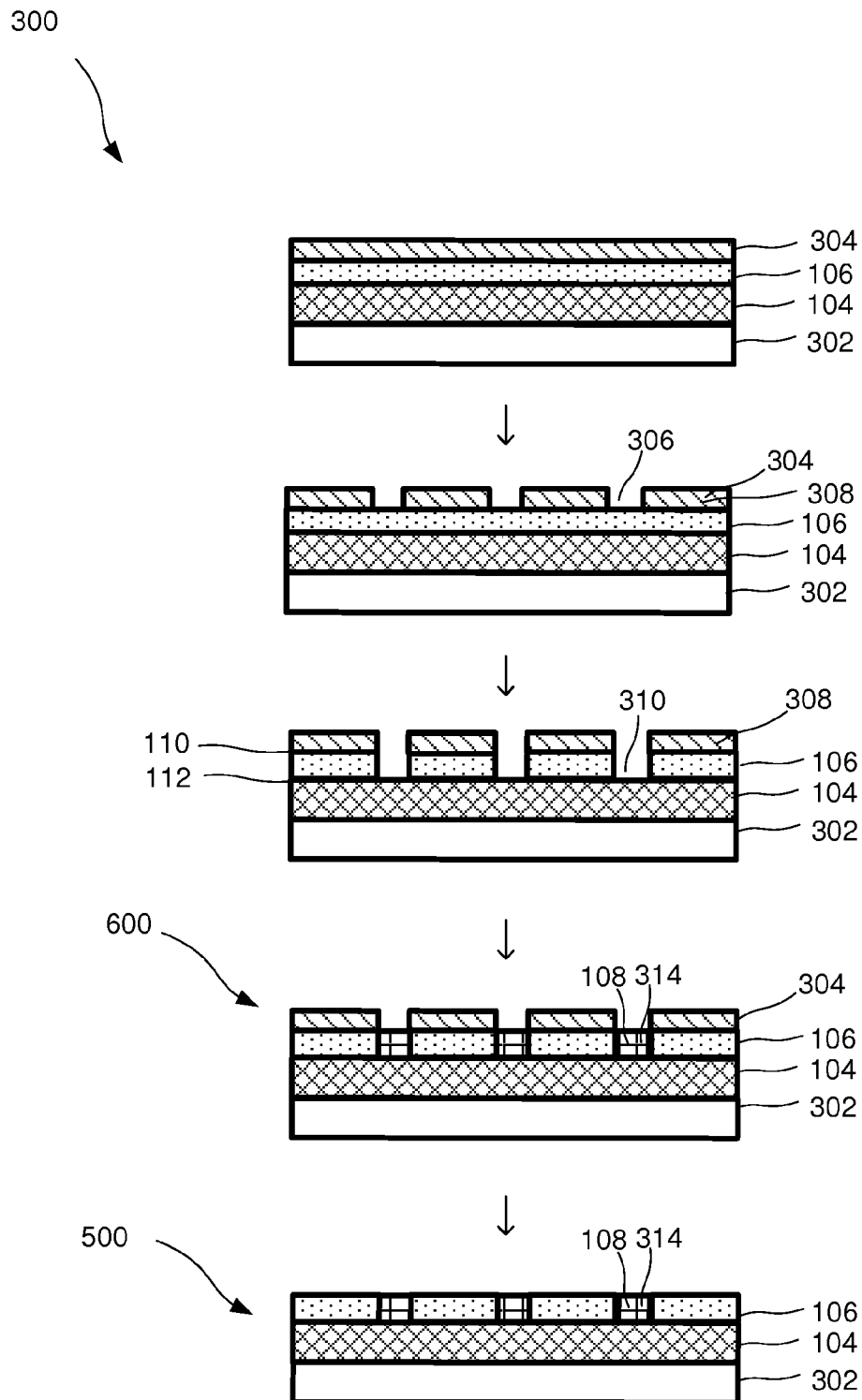


FIG. 4

5/6

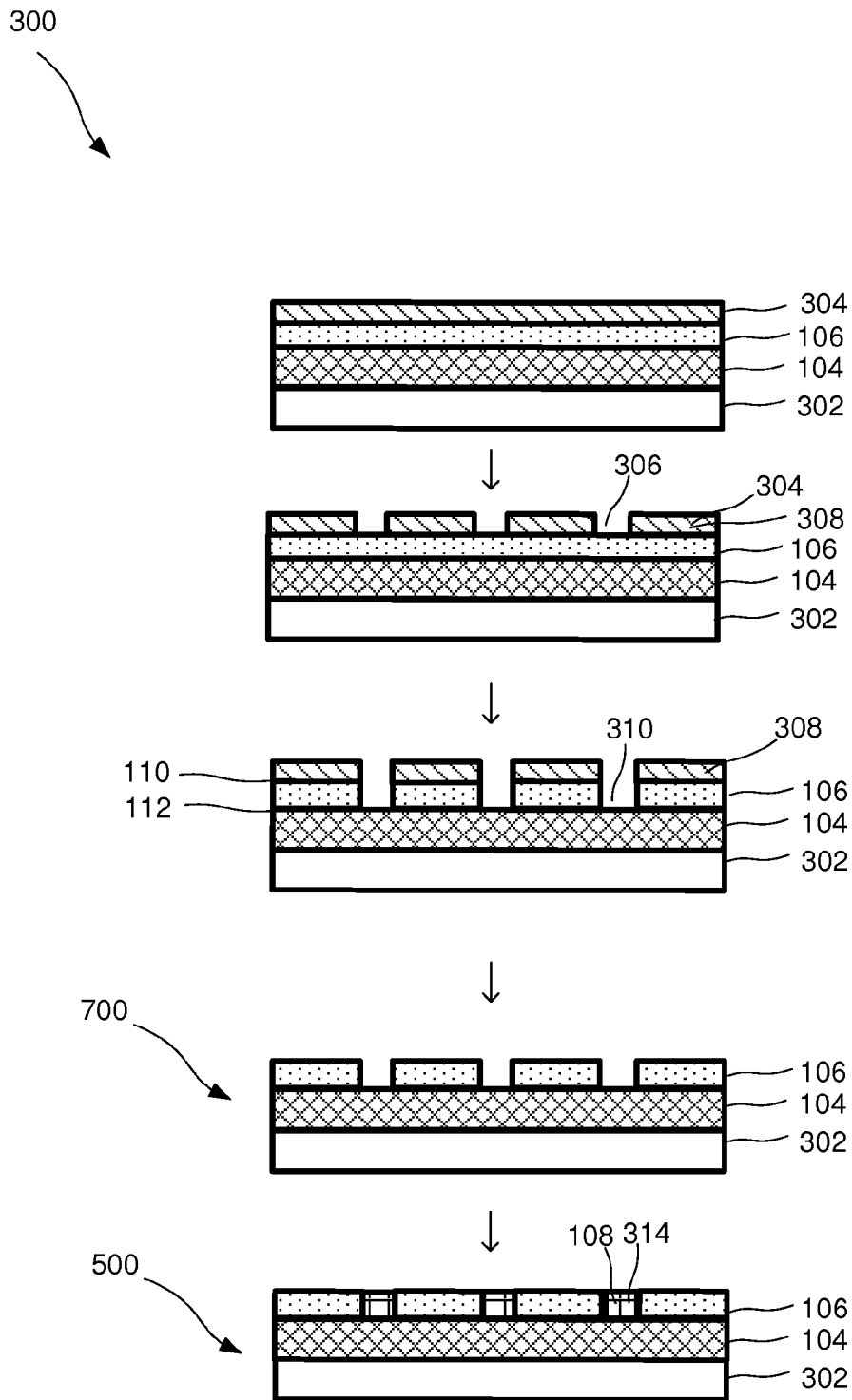


FIG. 5

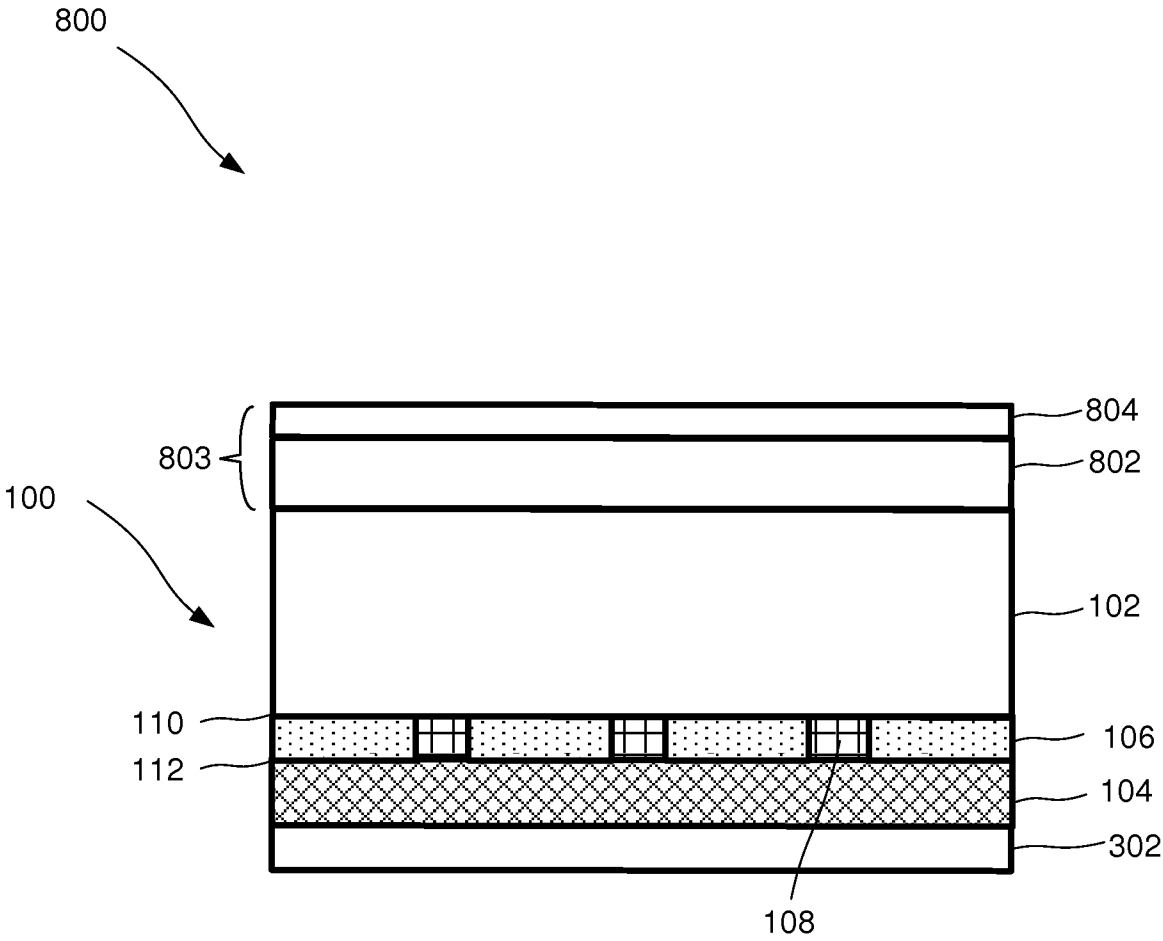


FIG. 6

INTERNATIONAL SEARCH REPORT

International application No
PCT/EP2016/057586

A. CLASSIFICATION OF SUBJECT MATTER
INV. H01L31/0224
ADD.

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

EPO-Internal, WPI Data

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 2014/216537 A1 (GRAFF JOHN [US]) 7 August 2014 (2014-08-07)	1,3,4,8
Y	the whole document	2,5-7
A		9-14
Y	----- US 2014/373917 A1 (KOREVAAR BASTIAAN ARIE [US] ET AL) 25 December 2014 (2014-12-25)	2,5-7
A	paragraphs [0068] - [0073], [0078] - [0086], [0107]; figures 7,13	1,3,4,8
A	----- US 2011/277833 A1 (MILLER MICHAEL N [US] ET AL) 17 November 2011 (2011-11-17)	1,8-14
	the whole document -----	



Further documents are listed in the continuation of Box C.



See patent family annex.

* Special categories of cited documents :

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"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art

"&" document member of the same patent family

Date of the actual completion of the international search

2 June 2016

Date of mailing of the international search report

08/06/2016

Name and mailing address of the ISA/

European Patent Office, P.B. 5818 Patentlaan 2
NL - 2280 HV Rijswijk
Tel. (+31-70) 340-2040,
Fax: (+31-70) 340-3016

Authorized officer

Voignier, Vincent

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No

PCT/EP2016/057586

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
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			US 2012260978 A1 18-10-2012
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			WO 2011143341 A2 17-11-2011
